

Dear customer

ROHM Co., Ltd. ("ROHM"), on the 1st day of April, 2024, has absorbed into merger with 100%-owned subsidiary of LAPIS Technology Co., Ltd.

Therefore, all references to "LAPIS Technology Co., Ltd.", "LAPIS Technology" and/or "LAPIS" in this document shall be replaced with "ROHM Co., Ltd." Furthermore, there are no changes to the documents relating to our products other than the company name, the company trademark, logo, etc.

Thank you for your understanding.

ROHM Co., Ltd. April 1, 2024



ML7425

Sub-GHz RF low-power transceiver IC

∎Overview

The ML7425 is a low-power sub-GHz radio transceiver LSI which integrates RF, IF, MODEM, and HOST interface into a single chip. RF frequency supports 145 to 1,020MHz range. In addition, a programable channel-selection filter can support a reception band of 1.7kHz to 1,200kHz. The ML7425 can be used for N-mode (169MHz), F-mode (434MHz), and S/T/C/R mode (868MHz) in the European telemetry standard (Wireless M-Bus), Japanese low-power security system radio stations and specified low-power radio stations (RCR STD-30, STD-T67, STD-T108), and worldwide Sigfox standards. The ML7425 includes IEEE802.15.4g and Wireless M-Bus packet handling functions.

Features

- Compliant with wireless regulations of each country
 - Japanese: RCR STD-30, ARIB STD-T67, ARIB STD-T108
 - Europe: ETSI EN 300 220, ETSI EN 54-25
 - North America: FCC CFR47 Part 15, FCC CFR47 Part 90, 24, 101
- Support standards
 - IEEE802.15.4g/15.4aa
 - Wi-SUN
 - Wireless M-BUS
 - Sigfox Revision 2.E
- RF Frequency
 - 145MHz to 170MHz
 - 210MHz to 250MHz
 - 280MHz to 340MHz
 - 415MHz to 510MHz
 - 835MHz to 1,020MHz
- Realizes high-precision modulation by direct modulation method of fractional-N PLL
- Support modulation scheme: 2(G)FSK/4(G)FSK, ASK, OOK, BPSK (Tx only)
- Suppot data rate : 0.1k to 1,200kbps (2FSK: 0.1k to 600kbps/4FSK: 0.2k to 1,200kbps)
- Equipped with encoding function of NRZ, Manchester, and 3 out of 6
- Equipped with data whitening function
- Equipped with a programmable channel filter function
- Equipped with a programmable frequency deviation function
- Built-in polarity reversal function for Tx/Rx data
- Equipped with TCXO direct input function (24 to 26MHz/48MHz to 52MHz)
- On-chip crystal oscillation circuit (24 to 26MHz/48MHz to 52MHz)
- Equipped with a load capacitance adjustment function for oscillation circuit pin
- Equipped with frequency fine adjustment function (Fine-tunable with fractional-N PLL)
- Built-in synchronous serial peripheral interface(SPI)
- Built-in Tx PA with power control function
- Equipped with Tx power fine adjustment function
- Equipped with automatic ramp control of Tx power
- Equipped with external Tx PA control function



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- Equipped with received signal strength indicator (RSSI) notification function and threshold judgment function
- Equipped with high speed carrier checking function
- Equipped with FEC Function
- Equipped with AFC Function
- Equipped with antenna diversity function
- Equipped with general purpose timer (2ch)
- Equipped with Test Pattern Generator (PN9, CW, 01-pattern, ALL "1", and ALL "0" are supported)
- Packet mode function
 - Supports IEEE802.15.4g Packet Format (Format C)
 - Supports Wireless M-Bus Packet Format (Format A/B)
 - Supports General-purpose Packet Format (Format C/D)
 - Supports packet length up to 255 bytes (Format A/B) and 2,047 bytes (Format C/D)
 - Built-in Tx FIFO (64 bytes) and Rx FIFO (64 bytes)
 - Detection preamble pattern setting function (Max.4 bytes)
 - Tx preamble length setting function (Max. 255 bytes)
 - SyncWord setting function (Max. 4 bytes x 2 patterns)
 - CRC Function (CRC32/CRC16/CRC8 selectable)
 - Address check function (Max. 13 bytes x 2 patterns)
 - Wireless M-Bus: C-field/M-field/A-field
 - *Proprietary packet format is possible depending on setting
 - Supports IEEE802.15.4g ModeSwitch Packet Format
- Supply voltage
 - 2.6V to 3.6V (when using DCDC) 1.8V to 3.6V (when not using DCDC)
- Operational temperature -40°C to 105°C (average operational temperature 70°C)
- Consumption current

Deep sleep mode		0.1 μΑ
Sleep mode		0.45 µA (registers retained)
At transmission	13dBm	27mA(Typ.) @3.3V, When using DCDC
At reception		11mA(Typ.) @3.3V, When using DCDC

- Package
 - 32-pin WQFN (5mm x 5mm) 0.5mm Lead-free, RoHS compliance

Product Name ML7425GD

- Application
 - Remote control Home, Building security Sensor networks Smart Meter Logistics Tracking Infrastructure Monitoring Monitoring system

■Block Diagram







32-pin WQFN (5mm x 5mm) 0.5mm pitch

ML7425

■Pin Description

Pin stat	us		Attribute defini	tion	
Ι	:	CMOS input	IS	:	Schmitt Trigger input pin
0	:	CMOS output	0	:	Digital output pin
OD	:	Open drain output	IOS	:	Digital input/output pin (Schmitt input)
Hi-Z	:	High impedance	IOA	:	Analog input/output pin
			IRF	:	RF input pin
			ORF	:	RF output pin
			VDD	:	Power supply pin
			GND	:	Ground

Pin No.	Pin Name	Attribute	Description
1	SDI	IS	SPI data input pin
2	SCEN	IS	SPI enable pin (H: disable, L: SPI enable)
3	SCLK	IS	SPI clock input pin
4	SDO	0	SPI data output pin
5	CAP_DIG	IOA	Pin for an internal LDO decoupling capacitor (Digital)
6	LDO_IN	VDD	Power supply pin (Regulator)
7	GND_DCDC	GND	Ground
8	DCDC_OUT	IOA	Switching regulator output pin (N.C. when DCDC is not used)
9	VDD_IO	VDD	Power supply pin (IO)
10	VREF	IOA	Pin for a decoupling capacitor 1
11	VREF2	IOA	Pin for a decoupling capacitor 2
12	N.C.(TEST1)	N.C.	Pin to open
13	VDD ANA	VDD	Power supply pin (Analog)
14	CAP PA	IOA	Pin for a decoupling capacitor (PA)
15	CAP PA2	IOA	Pin for an internal LDO decoupling capacitor (PA)
16	TXOUT	ORF	RF signal output pin
17	GND	GND	Ground
18	RXIN	IRF	RF signal input pin
19	CAP_RF	IOA	Pin for an internal LDO decoupling capacitor (RF)
20	N.C.(TEST2)	N.C.	Pin to open
21	VREF3	IOA	Pin for a decoupling capacitor 3
22	CAP_VCO	IOA	Pin for an internal LDO decoupling capacitor (VCO)
23	GND	GND	Ground
24	CAP_XO	IOA	Pin for an internal LDO decoupling capacitor (XO)
25	XOUT	IOA	Pin for connecting a crystal (TCXO input pin when TCXO is used)
26	XIN	IOA	Pin for connecting a crystal (N.C when TCXO is used)
27	GPIO3	IOS	Digital input/output pin (N.C. when GPIO3 is not used)
28	GPIO2	IOS	Digital input/output pin (N.C. when GPIO2 is not used)
29	GPIO1	IOS	Digital input/output pin (N.C. when GPIO1 is not used)
30	GPIO0	IOS	Digital input/output pin (N.C. when GPIO0 is not used)
31	PDN	IS	Power-down setting pin (H: Power-down mode, L: Normal mode)
32	RSTN	IS	Reset pin (H: Normal mode, L: Reset mode)

(Note)

Input pins (SDI, SCEN, SCLK, PDN, RSTN) must be logically Low or High.

Input/output pins (GPIO0 to 3) should be controlled by the host microcomputer.

The output pin (SDO) becomes an open-drain output pin after the reset is released. And this pin can be selected as a CMOS output or an open drain output. Please switch it according to the application.

			P	'in status			
Pin No.	Pin Name	[At deep sleep] PDN=H RSTN=L/H	【At reset】 PDN=L RSTN=L	[After reset release] PDN=L RSTN=H	[Normal mode] PDN=L RSTN=H	Attribute	Description
1	SDI	I	I	I	I	IS	SPI data input pin
2	SCEN	I	I	I	I	IS	SPI enable pin (H: disable, L: enable)
3	SCLK	I	I	I	I	IS	SPI clock input pin
4	SDO	Hi-Z	Hi-Z	OD	OD or O	0	SPI data output pin
27	GPIO3	Hi-Z	Hi-Z	0	l or O	IOS	Digital input/output pin
28	GPIO2	Hi-Z	Hi-Z	0	l or O	IOS	Digital input/output pin
29	GPIO1	Hi-Z	Hi-Z	0	l or O	IOS	Digital input/output pin
30	GPIO0	Hi-Z	Hi-Z	0	l or O	IOS	Digital input/output pin
31	PDN	I	I	I	I	IS	Power-down setting pin (H: Power-down mode, L: Normal mode)
32	RSTN	I	I	I	I	IS	Reset pin (H: Normal mode, L: Reset mode)

■Reference Schematic



Separate Transmission and Reception Configuration (Using Crystal Oscillator and Antenna switch)



Common Transmission and Reception Configuration (Using Crystal Oscillator, Not Using Antenna switch)



Separate Transmission and Reception Configuration (Using TCXO and Antenna switch)



Common Transmission and Reception Configuration (Using TCXO, Not Using Antenna switch)



Separate Transmission and Reception Configuration (Using Crystal Oscillator, Not using DCDC and Antenna switch)



Common Transmission and Reception Configuration (Using Crystal Oscillator, Not using DCDC, Not Using Antenna switch)

Electrical Characteristics

•Absolute Maximum Ratings

Item	Pin name	Condition	Rating	Unit
Supply voltage	VDD_IO、VDD_ANA	-	-0.3 to +4.6	V
Ground voltage	GND	-	-0.3 to +0.3	V
Digital input voltage	PDN, SDI, SCEN, SCLK, GPIO0 to 3	-	-0.3 to +4.6	V
Digital output voltage	GPIO0 to 3、SDO	-	-0.3 to +4.6	V
High-level output current	GPIO0 to 3、SDO	-	-8.0 (*1)	mA
Low-level output current	GPIO0 to 3、SDO	-	8.0 (*1)	mA
Voltage to Analog pins 1	DCDC_OUT, LDO_IN, CAP_PA, CAP_PA2, VREF	-	-0.3 to +4.6	V
Voltage to Analog pins 2	CAP_VCO, CAP_RF, CAP_DIG, CAP_XO, XIN, XOUT, VREF2, VREF3	-	-0.3 to +2.0	V
RF input voltage	RXIN	-	-0.3 to +2.0	V
RF output voltage	TXOUT	-	-0.3 to +4.6	V
RF input level	-	Antenna end of board (50Ω)	0	dBm
Power dissipation	-	Ta= +25°C	3.45	W
Storage temperature	-	-	-55~+150	°C

*1 The current flowing out of the LSI is specified as a minus sign.

Example: -1mA indicates that up to 1mA of current flows out of the LSI pin.

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•Reference Operating Conditions

Item	Symbol		Condition	Min.	Тур.	Max.	Unit
Power Supply Voltage (I/O,	VDDIO/	VDD_IO,	When not using DCDC	1.8	3.3	3.6	V
ANA)	VDD_ANA	VDD_ANA pin	When using DCDC	2.6	3.3	3.6	V
Operating temperature	Та		-		+25	+105	°C
Digital input Rising time	TIR	(*1)		-	-	20	ns
Digital input Falingl time	TIF	(*1)		-	-	20	ns
Digital output load	CDL	(*2)		-	-	20	pF
Deference cleak frequency				24	24	26	MHz
Reference clock frequency	FREF			48	48	52	MHz
Reference clock accuracy	ACREF		-		(*3)	(*3)	ppm
X'tal equivalent series resistance	ESR		-	-	-	50	ohm
TCXO input voltage	VTCXO	DC Cutoff *When TCXO op	otion is selected	0.8	-	1.5	Vpp
SPI clock input frequency	FSCLK	SCLK pin		0.032	2	16	MHz
SPI clock input duty ratio	DSCLK	SCLK pin		45	50	55	%
				145	-	170	MHz
				210	-	250	MHz
RF frequency	FRF		-	280	-	340	MHz
				415	-	510	MHz
				835	-	1020	MHz

*1 GPIO0, GPIO1, GPIO2, GPIO3, PDN, RSTN, SDI, SCEN, SCLK pin

*2 GPIO0, GPIO1, GPIO2, GPIO3, SDO pin

*3 The allowable frequency accuracy for transmission and reception are shown below.

In order to comply with various standards, please use the frequency accuracy according to the standards as shown in the table below.

Standard	Required frequency accuracy
ARIB STD-T108	±20 ppm
RCR STD-30 type III (Japanese)	±10 ppm
RCR STD-30 type IV (Japanese)	±4 ppm
Wireless M-Bus F mode	±16 ppm

Power Consumption

FREF =48 MHz, DCDC:ON

Item	Symbol	Condition		Min.	Тур.	Max.	Unit
Deep sleep current	IDD_DSLP	Deep sleep state (Not retaining Registers, all function halt)			0.1	50 (*1)	μA
Sleep current	IDD_SLP	Sleep state (retaining registers, retaining	-	0.45	120 (*2)	μA	
		DCDC=ON	-	1.2	3	mA	
Idle current		DCDC=OFF	DCDC=ON DCDC=OFF				mA
Py ourront	I _{DD920_RX1}	920MHz band, 2-FSK, 100kbps	DCDC=ON	-	11	25	mA
KX current	IDD920_RX2		DCDC=OFF		18	32	mA
Transmoot	IDD920_TX1	920MHz band, 2-FSK, 100kbps,	DCDC=ON	-	27	48	mA
	I _{DD920_TX2}	13 dBm output	DCDC=OFF	-	48	60	mA

(*1) For reference, maximum 0.8uA at 25°C

(*2) For reference, maximum 2.0uA at 25°C

•DC Characteristics

FREF =48MHz

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Voltage Input High	VIH	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	V _{DDIO} x 0.75	-	V _{DDIO}	V
Voltage Input Low	VIL	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	0	-	V _{DDIO} x 0.18	V
Schmitt Trigger Threshold High Level	VT+	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	-	1.2	V _{DDIO} x 0.75	V
Schmitt Trigger Threshold Low Level	VT-	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	V _{DDIO} x 0.18	0.8	-	V
Input lookage ourrent	IIH	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	-1	-	1	μA
input leakage current	IIL	RSTN, PDN, SDI, SCLK, SCEN, GPIO0/1/2/3 pin	Imminiation Min. Typ. Max. SDI, SCLK, SCEN, $V_{DDIO} \times 0.75$ - V_{DDIO} SDI, SCLK, SCEN, 0 - $V_{DDIO} \times 0.18$ SDI, SCLK, SCEN, - 1.2 $V_{DDIO} \times 0.75$ SDI, SCLK, SCEN, - 1.2 $V_{DDIO} \times 0.75$ SDI, SCLK, SCEN, - 1.2 $V_{DDIO} \times 0.75$ SDI, SCLK, SCEN, -1 - 1 '2/3 pin -1 - 1 '2/3 pin -1 - 1 '2/3 pin 0 - 0.25 - 6 - - '2/3 pin 0 - 9 - 9 - - - 9 - -	μA		
Tri-state	IOZH	SDO, GPIO0/1/2/3 pin	-1	-	1	μA
Output leakage current	IOZL	SDO, GPIO0/1/2/3 pin	-1	Typ. Max. - VDDIO - VDDIO x 0.18 1.2 VDDIO x 0.78 0.8 - - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 0.25 6 - 9 - 9 - 9 - 9 -	1	μA
Voltage Output High	VOH	SDO, GPIO0/1/2/3 pin IOH=-2mA	V _{DDIO} x 0.8	-	Vddio	V
Voltage Output Low	VOL	SDO, GPIO0/1/2/3 pin IOL=2mA	0	-	0.25	V
	CIN	Input pins	-	6	-	pF
	COUT	Output pins	-	9	-	pF
Pin capacitance	SymbolConditionMin.Typ.VIHRSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin $V_{DDIO} x 0.75$ -VILRSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin0-relVT+RSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin-1.2elVT-RSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin-1.2ntIIHRSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin-1-IILRSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin-1-IILRSTN, PDN, SDI, SCLK, SCEN, GPI00/1/2/3 pin-1-IOZHSDO, GPI00/1/2/3 pin-1-NoSDO, GPI00/1/2/3 pin-1-IOZLSDO, GPI00/1/2/3 pin0-vVOLSDO, GPI00/1/2/3 pin0-/CINInput pins-6COUTOutput pins-99CAIAnalog input pins-9	9	-	pF		
	CAI	Analog input pins	-	9	-	pF

•RF Characteristics

Condition:

- Reference Schematic: Separate transmission and reception configuration (Using TCXO)
- Measurement point: Evaluation board antenna end (excluding loss of antenna switch and SAW filters)
- Modulation scheme: 2-FSK
- Frequency: 920MHz band

[Transmission Characteristics]

FREF =48 MHz, DC	DC:ON					
Item	Condition	Min.	Тур.	Max.	Unit	
Tx output power	20mW (13dBm)	9	13	15	dBm	
Occupied bandwidth (99%)	99% power bandwidth, Pattern: PN9 Data rate: 100 kbps Freq. deviation ±50kHz, BT=0.5		150	-	250	kHz
Adjacent channel leakage power ratio [ACPR]	Data rate: 100kbps, Pattern: PN9 13dBm output, Freq. deviation: ±50kHz, BT=0.5 Leakage power ratio in 300kHz offset ± 100kHz	00kbps, Pattern: PN9 out, Freq. deviation: ±50kHz, BT=0.5 ower ratio in 300kHz offset ± 100kHz bandwidth				dBc
<u> </u>		710MHz or below	-	-	-36	dBm/100kHz
	At 13 dBm output Pattern: PN9 Data rate:100kbps Frog. doviation: +50kHz, BT=0.5	710-900MHz	-	-	-55	dBm/1MHz
		900-915MHz	-	-	-55	dBm/100kHz
0 · · · ·		915-930MHz	-	-	-36	dBm/100kHz
Spurious emission		930-1000MHz	-	-	-55	dBm/100kHz
		1000-1215MHz	-	-	-45	dBm/1MHz
		1215MHz or more	-	-	-30	dBm/1MHz
	Harmonic spurious level (2nd harmonic/3rd harmonic) At 13 dBm CW transmission ※When LC filter circuit is mounted			-	-30	dBm

[Receiver Characteristics]

FREF =48 MHz, DCDC:ON

Item	Conditior	า	Min.	Тур.	Max.	Unit
Min. receiver sensitivity	100kbps mode Center frequency: 920.7MHz BER<0.1% GFSK, Freq. deviation: ± 50kHz, BT=0.5		-	-106	-97	dBm
Adjacent channel selectivity	Ta=25°C, 100kbps mode Center frequency: 920 ZMHz	Interference signal: CW +400kHz offset	25	40	-	dB
(*1)	Desired signal: GFSK, Freq. deviation: ± 50kHz, BT=0.5	Interference signal: CW -400KHz offset	22	37	-	dB
	Ta=25°C, 100kbps mode	Interference signal: CW 2MHz offset	36	55	-	dB
	Center-frequency: 920.7MHz Desired signal: GFSK, Freq. deviation: ± 50kHz, BT=0.5	Interference signal: CW 10MHz offset	41	65	-	dB
Min. energy detection level (ED value)	RFmin in ED characteristics diagra 100kbps mode Center frequency: 920.7MHz Channel filter band =200kHz settin	RFmin in ED characteristics diagram (*2) 100kbps mode Center frequency: 920.7MHz Channel filter band =200kHz setting			-100	dBm
Energy detection range	Dynamic range in ED characteristic 100kbps mode Center frequency: 920.7MHz Channel filter band =200kHz settin	55	65	-	dB	
Spurious emission level			-	-	-57	dBm

*1. The Measuring condition for interference-related characteristics is as follows:

Set the desired signal as [the level with BER = 0.1% (= reference sensitivity) + 3 dB], change the interference signal level to find the level at which becomes BER = 0.1%, and stipulate as U/D [dB] = (interference signal level) - (desired signal input level).

*2. ED characteristic diagram is shown below.



ED Characteristic Diagram

[Note]

The characteristics may be degraded when using channels near the multiplication of the reference clock or the multiplication of the reference clock divided by 2 or 4.

• Reference

•SPI Interface Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
SCLK clock frequency	Fsclk		0.032	2	16	MHz
SCEN input setup time	TSCENSU		30	-	-	ns
SCEN input hold time	TSCENH		30	-	-	ns
SCLK high pulse width	TSCLKH		31	-	-	ns
SCLK low pulse width	TSCLKL	Load capacitance	31	-	-	ns
SDI input setup time	TSDISU	CL=20pF	5	-	-	ns
SDI input hold time	TSDIH		15	-	-	ns
SCEN negate period	T _{SCENNI}		200	-	-	ns
SDO output delay time	T _{SDODLY}		-	-	25	ns
SDO output setup time	Tsdosu		6	_	_	ns

[Note]

All timing measurement points are at VDDIO* 20% and VDDIO*80%. Please refer the required setup time of host MCU for SDO output.



•DIO Interface Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
DIO input setup time	TDISU		DataRate*1/4	-	-	μs
DIO input hold time	T _{DIH}		0	-		ns
DIO output delay time	T _{DODLY}		-	-	DataRate*1/10	μs
DIO output hold time	Трон		20	-	-	ns
DCLK frequency accuracy (*1) (TX)	Fdclk_tx	Load capacitance CI =20pF	 Clock freq. deviation 	-	+ Clock freq. deviation	kHz
DCLK frequency accuracy (*2) (RX)	Fdclk_rx	00p.	-30	-	+30	%
DCLK output duty ratio (TX)	Ddclk_tx		45	-	55	%
DCLK output duty ratio (RX)	Ddclk_rx		30	-	70	%

*1 When no decimal point occurs in calculating the Tx data rate value, Max. and Min. values of Tx DCLK frequency are the reference clock frequency deviations.

*2 Min. and max. of Rx DCLK frequency indicates the amount of jitter in the regenerated clock generated from the received signal (when synchronization is established).

[Note]



Clock Output Characteristics

ML7406 has clock output function. The clock is output through GPIO1 pin as initialized setting.

Item	Symbol	Condition		Min.	Тур.	Max.	Unit
Clock output frequency	Fclkout	Load capacitance CL=20 pF		FREF/8164 (0.0059) (*2)	FREF/740 (0.0649) (*2)	FREF/2 (24) (*2)	MHz
Clock output duty ratio (*1)	Dclkout	Load capacitance CL=20 pF	FREF/2 (24)	25	-	75	%
			FREF/6 (8) (*2)	33	-	67	%
			Except above	47	50	53	%

*1 When set to FREF/2, the duty ratio is High:Low = 1:3. When set to FREF/6, the duty ratio is High:Low = 1:2 . *2 The values in parentheses are the values at FREF =48MHz.

[Note]



Reset Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
RSTN release delay time (power on period)	T _{RDL1}	All power pins After Power On	1	-	-	ms
RSTN pulse period (when booting from VDD_IO/VDD_ANA = 0V)	T _{RPW1}		0.5	-	-	ms
RSTN pulse-time 2 (*1) (when booting from VDD_IO/VDD_ANA ≠ 0V)	T _{RPW2}		1	-	-	ms
RSTN input delay time	T _{RDL2}	After VDD_IO/VDD_ANA>1.8	1	-	-	μs
RSTN input delay time after Power on (start from VDD_IO/VDD_ANA = 0V)	T _{RDL3}	From the rising edge of T _{RDL1} to the falling edge of TRPW1	100	-	-	μs

(*1) When starting from VDD_IO/VDD_ANA \neq 0V, input Low pulse to RSTN pin after VDD_IO/VDD_ANA exceeds 1.8V.

[Note]



•Deep Sleep Mode Characteristics

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
PDN rising edge delay time	T _{RPFD}	VDD_IO/VDD_ANA ="H"	10	-	-	ms
PDN assert time (Deep sleep mode period)	TRPASS	VDD_IO/VDD_ANA ="H"	1.2	-	-	ms
RSTN release delay time	T _{REFD}	VDD_IO/VDD_ANA ="H"	1	-	-	ms

[Note]



• Power-on Characteristics

Item	Symbol	Condition	Min. Typ.		Max.	Unit
Power up time	T _{PWON}	Power on state (VDD_IO/VDD_ANA pin)	0.1	-	5	ms

[Note]



■Revision History

		Pa	ge	
Document No.	Issue Date	Previous	Current	Change Contents
		Edition	Edition	
FEDL7425-01	2023/12/11	-	-	Initial release
FEDL7425-02	2024/03/19	1	1	Unify the names of radio stations and radio regulations
		7–8	7–9	Updating the reference circuit diagram and adding the common configuration circuit diagram
		12	13	Updating the maximum value of the power supply current characteristic
		22	23	Changed wording of Notes

Notes

- 1) When using LAPIS Technology Products, refer to the latest product information and ensure that usage conditions (absolute maximum ratings^{*1}, recommended operating conditions, etc.) are within the ranges specified. LAPIS Technology disclaims any and all liability for any malfunctions, failure or accident arising out of or in connection with the use of LAPIS Technology Products outside of such usage conditions specified ranges, or without observing precautions. Even if it is used within such usage conditions specified ranges, semiconductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury, fire or the other damage from break down or malfunction of LAPIS Technology Products, please take safety at your own risk measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures.
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